BFR94AW

NPN 5 GHz wideband transistor

Rev. 1 — 29 October 2010

Product data sheet

1. Product profile

1.1 General description

Silicon NPN transistor encapsulated in a plastic SOT323 (S-mini) package. The BFR94AW uses the same crystal as the SOT23 version, BFR94A.

1.2 Features and benefits

- High power gain
- Gold metallization ensures excellent reliability
- AEC-Q101 qualified

1.3 Applications

RF amplifiers, mixers and oscillators with signal frequencies up to 1 GHz

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	-	20	V
V_{CEO}	collector-emitter voltage	open base	-	-	15	V
I_{C}	collector current		-	-	25	mA
P _{tot}	total power dissipation	$T_{sp} \le 93 ^{\circ}C$	-	-	300	mW
h _{FE}	DC current gain	$I_C = 15 \text{ mA}; V_{CE} = 10 \text{ V}$	65	90	135	
C _{re}	feedback capacitance	$I_C = 0$ mA; $V_{CE} = 10$ V; f = 1 MHz; $T_{amb} = 25$ °C	-	0.35	-	pF
f _T	transition frequency	$I_C = 15 \text{ mA}; V_{CE} = 10 \text{ V};$ f = 500 MHz	3.5	5	-	GHz
G_UM	unilateral power gain	$I_C = 15 \text{ mA}; V_{CE} = 10 \text{ V};$ $T_{amb} = 25 ^{\circ}\text{C}$				
		f = 1 GHz	-	14	-	dB
		f = 2 GHz	-	8	-	dB
NF	noise figure	$I_C = 5$ mA; $V_{CE} = 10$ V; $f = 1$ GHz; $\Gamma_S = \Gamma_{opt}$	-	2	-	dB
Tj	junction temperature		-	-	150	°C



2. Pinning information

Table 2. Pinning

	•		
Pin	Description	Simplified outline	Graphic symbol
1	base		
2	emitter	3	3
3	collector	1 2	2 —
			sym026

3. Ordering information

Table 3. Ordering information

Type number	Package			
	Name	Description	Version	
BFR94AW	-	plastic surface-mounted package; 3 leads	SOT323	

4. Marking

Table 4. Marking

Type number	Marking code	Description
BFR94AW	XG*	* = p : made in Hong Kong
		* = t : made in Malaysia

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	20	V
V_{CEO}	collector-emitter voltage	open base	-	15	V
V_{EBO}	emitter-base voltage	open collector	-	2	V
I _C	collector current		-	25	mA
P _{tot}	total power dissipation	$T_{sp} \le 93 ^{\circ}C$; see Figure 1	<u>[1]</u> _	300	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	+150	°C

^[1] T_{sp} is the temperature at the solder point of the collector pin.

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6. Thermal characteristics

Table 6	Thermal	charact	oriction

Symbol	Parameter	Conditions		Тур	Unit
$R_{th(j\text{-sp})}$	thermal resistance from junction to solder point	$T_{sp} \le 93 ^{\circ}C$	<u>[1]</u>	190	K/W

^[1] T_{sp} is the temperature at the solder point of the collector pin.

7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I_{CBO}	collector-base cut-off current	$I_E = 0 \text{ A}; V_{CB} = 10 \text{ V}$	-	-	50	nA
h _{FE}	DC current gain	$I_C = 15 \text{ mA}; V_{CE} = 10 \text{ V}$	65	90	135	
C _c	collector capacitance	$I_E = i_e = 0 \text{ A}; V_{CB} = 10 \text{ V}; f = 1 \text{ MHz}$	-	0.6	-	рF
C _e	emitter capacitance	$I_C = I_c = 0 \text{ A}; V_{EB} = 0.5 \text{ V}; f = 1 \text{ MHz}$	-	0.9	-	pF
C _{re}	feedback capacitance	$I_C = 0$ mA; $V_{CE} = 10$ V; $f = 1$ MHz; $T_{amb} = 25$ °C	-	0.35	-	pF
f _T	transition frequency	$I_C = 15 \text{ mA}; V_{CE} = 10 \text{ V}; f = 500 \text{ MHz}$	3.5	5	-	GHz
G_UM	unilateral power gain	I_C = 15 mA; V_{CE} = 10 V; T_{amb} = 25 °C	<u>[1]</u>			
		f = 1 GHz	-	14	-	dB
		f = 2 GHz	-	8	-	dB
NF	noise figure	I_C = 5 mA; V_{CE} = 10 V; Γ_S = Γ_{opt}				
		f = 1 GHz	-	2	-	dB
		f = 2 GHz	-	3	-	dB

^[1] $\;\;$ G_{UM} is the maximum unilateral power gain, assuming S_{12} is zero and

$$G_{UM} = 10 \log \frac{\left|S_{2I}\right|^2}{(1 - \left|S_{II}\right|^2)(1 - \left|S_{22}\right|^2)} dB.$$

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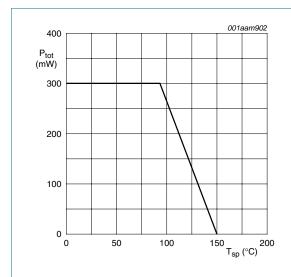


Fig 1. Power derating curve

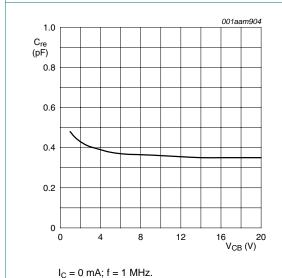
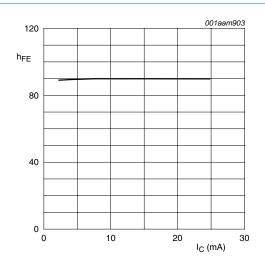
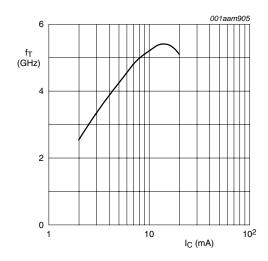


Fig 3. Feedback capacitance as a function of collector-base voltage; typical values



 $V_{CE} = 10 \text{ V}.$

Fig 2. DC current gain as a function of collector current; typical values



 V_{CE} = 5 V; f = 500 MHz; T_{amb} = 25 °C.

Fig 4. Transition frequency as a function of collector current; typical values

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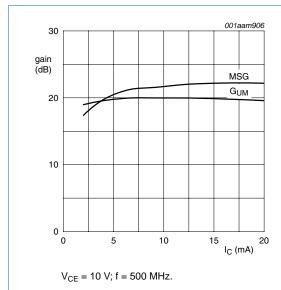


Fig 5. Gain as a function of collector current; typical values

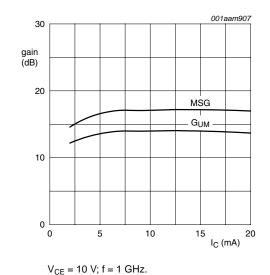


Fig 6. Gain as a function of collector current; typical values

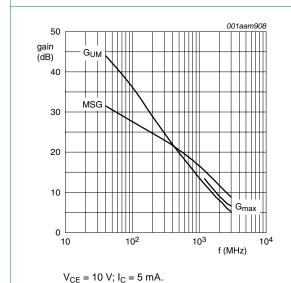


Fig 7. Gain as a function of frequency; typical values

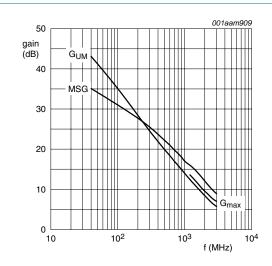


Fig 8. Minimum noise figure as a function of frequency; typical values

 $V_{CE} = 10 \text{ V}; I_{C} = 5 \text{ mA}.$

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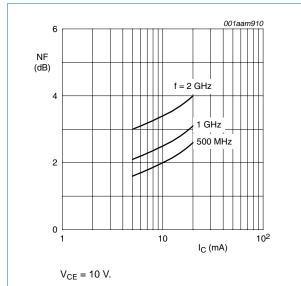


Fig 9. Minimum noise figure as a function of collector current; typical values

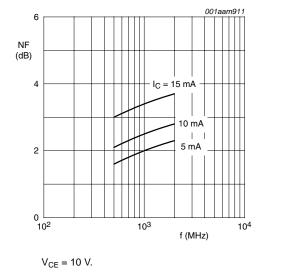
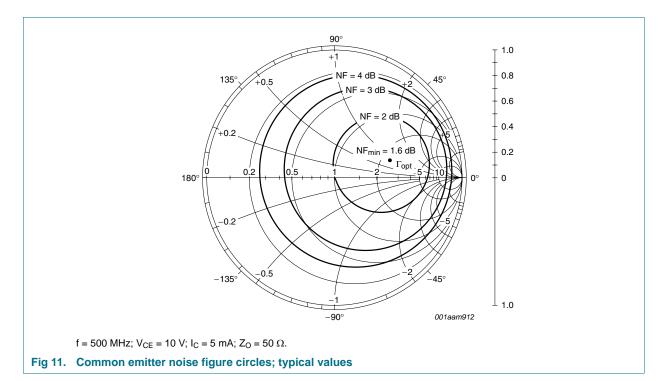
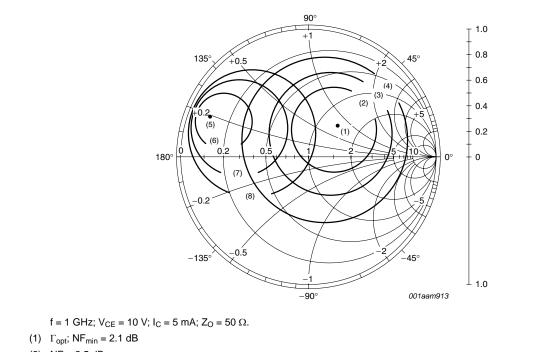


Fig 10. Minimum noise figure as a function of frequency; typical values



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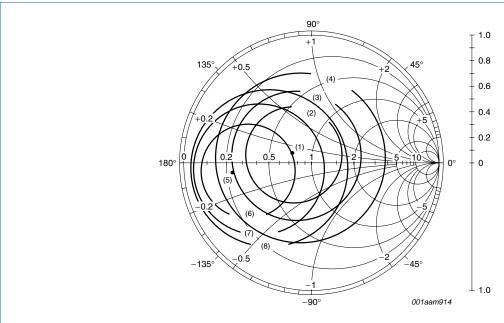
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- (2) NF = 2.5 dB
- (3) NF = 3 dB
- (4) NF = 4 dB
- (5) Γ_{ms} ; $G_{max} = 15.7 \text{ dB}$
- (6) G = 15 dB
- (7) G = 14 dB
- (8) G = 13 dB

Fig 12. Common emitter noise figure circles; typical values

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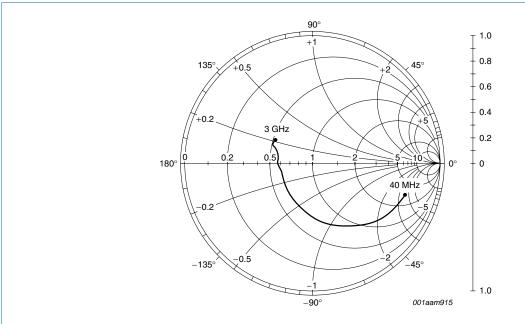


f = 2 GHz; $V_{CE} = 10 \text{ V}$; $I_C = 5 \text{ mA}$; $Z_O = 50 \Omega$.

- (1) Γ_{opt} ; NF_{min} = 3 dB
- (2) NF = 3.5 dB
- (3) NF = 4 dB
- (4) NF = 5 dB
- (5) Γ_{ms} ; $G_{max} = 9.1 \text{ dB}$
- (6) G = 8 dB
- (7) G = 7 dB
- (8) G = 6 dB

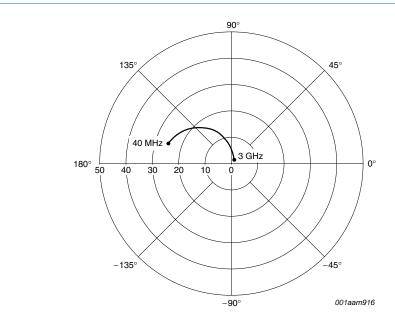
Fig 13. Common emitter noise figure circles; typical values

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 V_{CE} = 10 V; I_{C} = 15 mA; Z_{O} = 50 $\Omega.$

Fig 14. Common emitter input reflection coefficient (S₁₁); typical values



 V_{CE} = 10 V; I_{C} = 15 mA.

Fig 15. Common emitter forward transmission coefficient (S₂₁); typical values

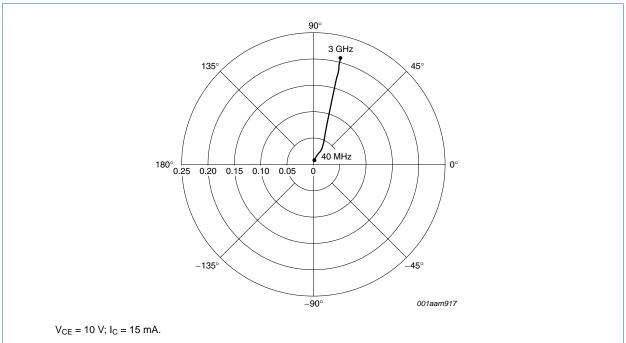
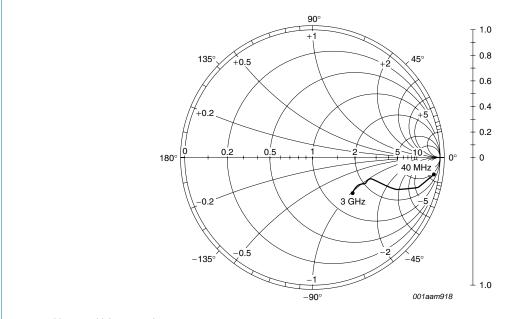


Fig 16. Common emitter reverse transmission coefficient (S₁₂); typical values



 $V_{CE} = 10 \text{ V}; I_{C} = 15 \text{ mA}.$

Fig 17. Common emitter output reflection coefficient (S₂₂); typical values

8. Package outline

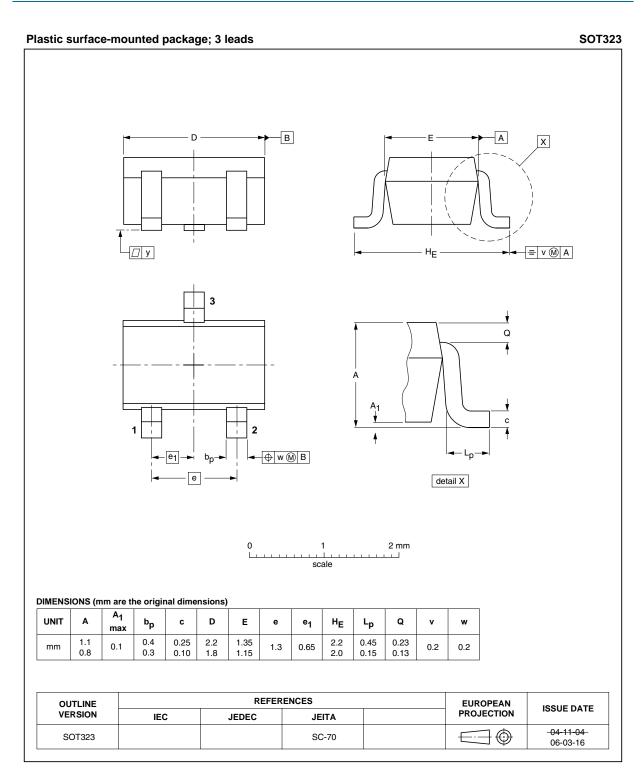


Fig 18. Package outline SOT323

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9. Abbreviations

Table 8. Abbreviations

Acronym	Description
MSG	Maximum Stable Gain
NPN	Negative Positive Negative
RF	Radio Frequency

10. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BFR94AW v.1	20101029	Product data sheet	-	-

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Date of release: 29 October 2010

Document identifier: BFR94AW

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